Integrated Relay, Inductive Load Driver

This device is used to switch inductive loads such as relays, solenoids incandescent lamps, and small DC motors without the need of a free-wheeling diode. The device integrates all necessary items such as the MOSFET switch, ESD protection, and Zener clamps. It accepts logic level inputs thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

Features

- Provides a Robust Driver Interface Between D.C. Relay Coil and Sensitive Logic Circuits
- Optimized to Switch Relays of 12 V Rail
- Capable of Driving Relay Coils Rated up to 6.0 W at 12 V
- Internal Zener Eliminates the Need of Free-Wheeling Diode
- Internal Zener Clamp Routes Induced Current to Ground for Quieter Systems Operation
- Low V_{DS(ON)} Reduces System Current Drain
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Typical Applications

- Telecom: Line Cards, Modems, Answering Machines, FAX
- Computers and Office: Photocopiers, Printers, Desktop Computers
- Consumer: TVs and VCRs, Stereo Receivers, CD Players, Cassette Recorders
- Industrial: Small Appliances, Security Systems, Automated Test Equipment, Garage Door Openers



ON Semiconductor®

www.onsemi.com

MARKING DIAGRAMS



SOT-23 CASE 318 STYLE 21



JW5 = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)



SC-74 CASE 318F STYLE 7



JW5 = Specific Device Code

M = Date Code

= Pb-Free Package

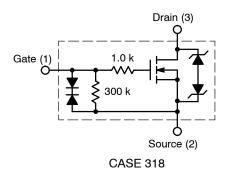
(Note: Microdot may be in either location)

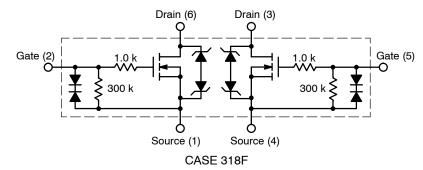
ORDERING INFORMATION

Device	Package	Shipping [†]
NUD3112LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SZNUD3112LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NUD3112DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel
SZNUD3112DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

INTERNAL CIRCUIT DIAGRAMS





MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise specified)

Symbol	Rating		Value	Unit
V _{DSS}	Drain to Source Voltage - Continuous		14	V _{dc}
V _{GS}	Gate to Source Voltage – Continuous		6	V _{dc}
I _D	Drain Current - Continuous		500	mA
Ez	Single Pulse Drain-to-Source Avalanche Energy (T _{Jinitial} = 25°C)		50	mJ
TJ	Junction Temperature		150	°C
T _A	Operating Ambient Temperature		-40 to 85	°C
T _{stg}	Storage Temperature Range		-65 to +150	°C
P _D	Total Power Dissipation (Note 1) Derating Above 25°C	SOT-23	225 1.8	mW mW/°C
P _D	Total Power Dissipation (Note 1) Derating Above 25°C	SC-74	380 3.0	mW mW/°C
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient (Note 1)	SOT-23 SC-74	556 329	°C/W
ESD	Human Body Model (HBM) According to EIA/JESD22/A114		2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Mounted onto minimum pad board.

$\textbf{TYPICAL ELECTRICAL CHARACTERISTICS} \ (T_{A} = 25^{\circ}\text{C unless otherwise noted})$

Symbol	Characteristic	Min	Тур	Max	Unit
OFF CHAR	ACTERISTICS			1	
V _{BRDSS}	Drain to Source Sustaining Voltage (Internally Clamped) (ID = 10 mA)	14	16	17	V
B _{VGSO}	I _g = 1.0 mA	-	-	8	V
I _{DSS}	Drain to Source Leakage Current $ (V_{DS} = 12 \text{ V} \text{ , } V_{GS} = 0 \text{ V}, T_A = 25^{\circ}\text{C}) $ $ (V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, T_A = 85^{\circ}\text{C}) $		- -	20 40	μΑ
I _{GSS}	Gate Body Leakage Current $(V_{GS} = 3.0 \text{ V}, V_{DS} = 0 \text{ V})$ $(V_{GS} = 5.0 \text{ V}, V_{DS} = 0 \text{ V})$		- -	35 65	μΑ
ON CHARA	CTERISTICS	•		•	
V _{GS(th)}	Gate Threshold Voltage $ (V_{GS} = V_{DS}, I_D = 1.0 \text{ mA}) $ $ (V_{GS} = V_{DS}, I_D = 1.0 \text{ mA}, T_A = 85^{\circ}\text{C}) $	0.8 0.8	1.2 -	1.4 1.4	V
R _{DS(on)}	Drain to Source On–Resistance $ \begin{aligned} &(I_D=250 \text{ mA, V}_{GS}=3.0 \text{ V}) \\ &(I_D=500 \text{ mA, V}_{GS}=3.0 \text{ V}) \\ &(I_D=500 \text{ mA, V}_{GS}=5.0 \text{ V}) \\ &(I_D=500 \text{ mA, V}_{GS}=5.0 \text{ V}) \\ &(I_D=500 \text{ mA, V}_{GS}=3.0 \text{ V, T}_{A}=85^{\circ}\text{C}) \\ &(I_D=500 \text{ mA, V}_{GS}=5.0 \text{ V, T}_{A}=85^{\circ}\text{C}) \end{aligned} $	- - - -	- - - -	1.2 1.3 0.9 1.3 0.9	Ω
I _{DS(on)}	Output Continuous Current $(V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V})$ $(V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V}, T_{A} = 85^{\circ}\text{C})$		400 -	- -	mA
9FS	Forward Transconductance (V _{OUT} = 12.0 V, I _{OUT} = 0.25 A)	350	490	-	mmhos

TYPICAL ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

	()				
Symbol	Characteristic	Min	Тур	Max	Unit
DYNAMIC (CHARACTERISTICS	•			
C _{iss}	Input Capacitance (V _{DS} = 12 V, V _{GS} = 0 V, f = 10 kHz)	-	23	_	pF
C _{oss}	Output Capacitance (V _{DS} = 12 V, V _{GS} = 0 V, f = 10 kHz)	-	30	_	pF
C _{rss}	Transfer Capacitance (V_{DS} = 12.0 V, V_{GS} = 0 V, f = 10 kHz)	-	7	_	pF

SWITCHING CHARACTERISTICS

Symbol	Characteristic	Min	Тур	Max	Units
t _{PHL} t _{PLH}	Propagation Delay Times: High to Low Propagation Delay; Figure 1 (V_{DS} = 12 V, V_{GS} = 5.0 V) Low to High Propagation Delay; Figure 1 (V_{DS} = 12 V, V_{GS} = 5.0 V)		21 91		nS
t _f	Transition Times: Fall Time; Figure 1 (V_{DS} = 12 V, V_{GS} = 5.0 V) Rise Time; Figure 1 (V_{DS} = 12 V, V_{GS} = 5.0 V)	- -	36 61	- -	nS

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

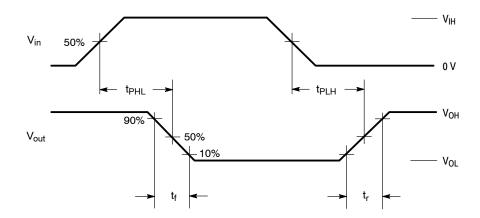
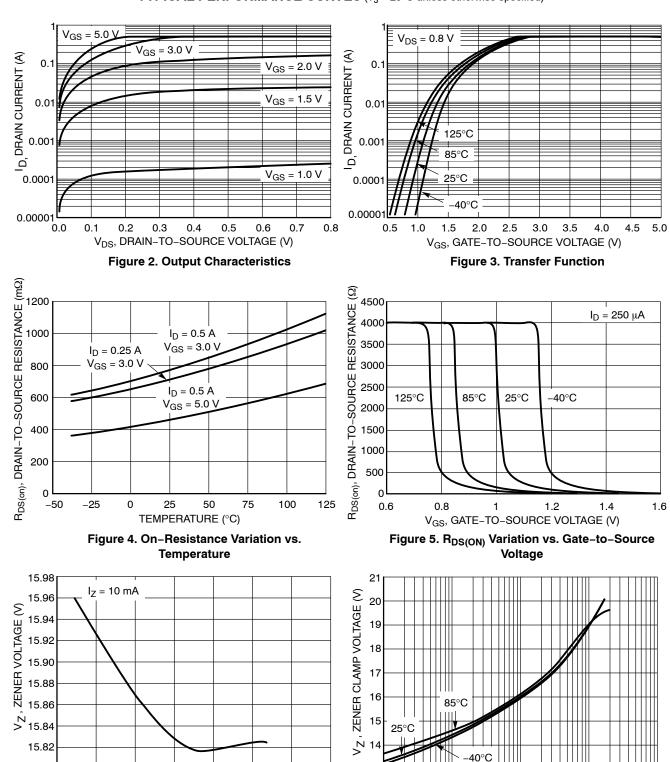


Figure 1. Switching Waveforms

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise specified)



TEMPERATURE (°C)

Figure 6. Zener Voltage vs. Temperature

25

50

75

100

15.80

-50

-25

Figure 7. Zener Clamp Voltage vs. Zener Current

10

IZ, ZENER CURRENT (mA)

1000

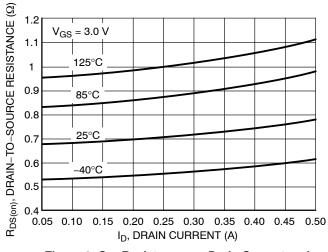
100

125

13

0.1

TYPICAL PERFORMANCE CURVES ($T_J = 25$ °C unless otherwise specified)



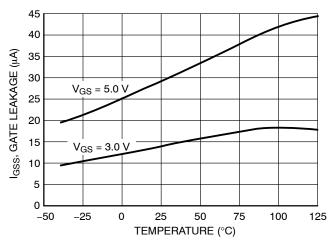


Figure 8. On-Resistance vs. Drain Current and Temperature

Figure 9. Gate Leakage vs. Temperature

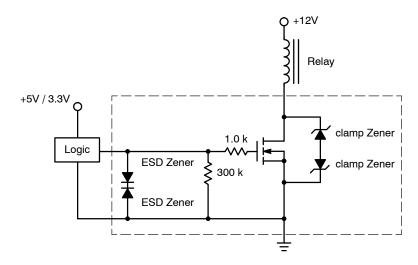
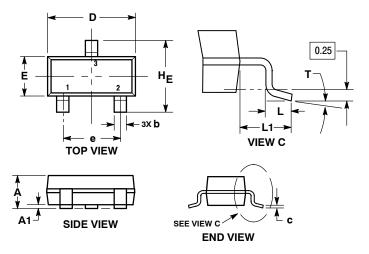


Figure 10. Typical Application Circuit

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**



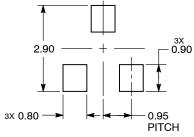
- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF
 THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR GATE BURRS.

	M	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.039	0.044	
A1	0.01	0.06	0.10	0.000	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.017	0.020	
С	0.08	0.14	0.20	0.003	0.006	0.008	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.080	
L	0.30	0.43	0.55	0.012	0.017	0.022	
L1	0.35	0.54	0.69	0.014	0.021	0.027	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
Т	0°		10 °	0 °		10 °	

- STYLE 21:
 PIN 1. GATE
 2. SOURCE
 3. DRAIN

RECOMMENDED SOLDERING FOOTPRINT*

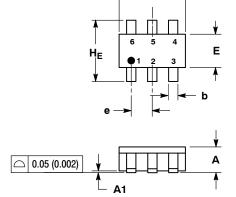


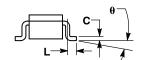
DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SC-74 CASE 318F-05 ISSUE N





NOTES:

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

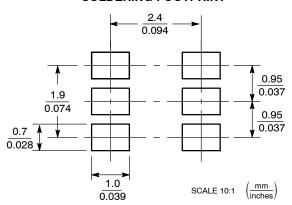
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.90	1.00	1.10	0.035	0.039	0.043	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.25	0.37	0.50	0.010	0.015	0.020	
c	0.10	0.18	0.26	0.004	0.007	0.010	
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	1.30	1.50	1.70	0.051	0.059	0.067	
е	0.85	0.95	1.05	0.034	0.037	0.041	
L	0.20	0.40	0.60	0.008	0.016	0.024	
HE	2.50	2.75	3.00	0.099	0.108	0.118	
θ	0°	-	10°	0°	-	10°	

STYLE 7: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2

- SOURCE 2
- GATE 2
- 5. 6.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor:

NUD3112DMT1G NUD3112LT1G SZNUD3112DMT1G SZNUD3112LT1G